

Spin Splitting in GaAs (100) Two-Dimensional Holes Revisited

B. Habib, E. Tutuc, S. Melinte, M. Shayegan, D. Wasserman, S. A. Lyon
Department of Electrical Engineering, Princeton University, Princeton, NJ 08544, USA

R. Winkler

Institut für Festkörperphysik, Universität Hannover, Appelstr. 2, D-30167 Hannover, Germany
 (Dated: February 2, 2008)

We measured Shubnikov-de Haas (SdH) oscillations in GaAs (100) two-dimensional holes to determine the inversion asymmetry-induced spin splitting. The Fourier spectrum of the SdH oscillations contains two peaks, at frequencies f_- and f_+ , that correspond to the hole densities of the two spin subbands and a peak, at frequency f_{tot} , corresponding to the total hole density. In addition, the spectrum exhibits an anomalous peak at $f_{\text{tot}}/2$. We also determined the effective masses of the two spin subbands by finding the inverse transform of the Fourier spectrum in the vicinity of f_- and f_+ , and then analyzing the temperature dependence of the SdH oscillations for each subband. We discuss our results in light of self-consistent calculations and previous experiments.

PACS numbers: Valid PACS appear here

In a solid that lacks inversion symmetry, the spin-orbit (SO) interaction leads to a lifting of the spin degeneracy of the energy bands, even in the absence of an applied magnetic field. In such a solid, the energy bands at finite wave vectors are split into two spin subbands with different energy surfaces, populations, and effective masses. This so-called zero-field spin splitting is particularly important for semiconductor holes because they typically have much smaller kinetic energies than electrons. The problem of inversion asymmetry-induced spin splitting in two-dimensional (2D) carrier systems in semiconductor heterojunctions and quantum wells [1, 2, 3] has become of renewed interest recently [4] because of the possible use of such systems in realizing spintronic devices such as a spin field-effect transistor [5, 6], and for studying fundamental phenomena such as the spin Berry phase [7, 8].

GaAs 2D holes in modulation-doped GaAs/AlGaAs heterostructures [1, 2] provide an attractive system for these studies as they can have high low-temperature mobilities and a strong SO interaction that is tunable via the application of gate bias [9, 10]. Recent work in these systems has concentrated primarily on 2D holes that are fabricated, via molecular beam epitaxy (MBE), on GaAs (311)A substrates. The main advantage of using (311)A substrates, rather than the more commonly used (100) substrates, is that one can use Si as a p -type dopant in the MBE growth. The standard p -type dopant for MBE growth on GaAs (100) is Be. Unlike Si, however, Be has a tendency to diffuse and migrate under typical MBE growth conditions and, as a result, fabrication of high-quality GaAs (100) 2D holes has been challenging. On the other hand, because of a higher symmetry, the band structure for (100) GaAs 2D holes is simpler than for (311)A [4]. It is therefore desirable to study the problem of spin splitting in GaAs (100) 2D hole systems. We have been able to fabricate such 2D systems with reasonably high mobilities, and report here our measurements of their spin splitting and of the hole effective mass, and

the comparison of the experimental data with the results of state-of-the-art energy band calculations [4, 11].

The holes in GaAs (100) were in fact the first 2D system in which the inversion asymmetry-induced spin splitting was observed experimentally using SdH oscillations [1, 2]. The oscillations in 2D holes confined to GaAs/AlGaAs heterojunctions revealed a beating pattern, indicating the presence of two spin subbands with different hole densities [2]. The spin splitting was inferred from a change in the frequency of the oscillations above a certain magnetic field. The temperature dependence of the amplitude of the oscillations along with the assumption that the spin subbands are parabolic was used to deduce their masses [2]. Although the results of these experiments were in qualitative agreement with the calculations that followed, some questions remain, particularly regarding the effective mass values [12, 13, 14, 15]. In our study, we revisit the spin splitting in GaAs (100) 2D holes via a careful analysis of the beating pattern in SdH oscillations. We employ Fourier transform (FT) techniques to determine the temperature dependence of the amplitude of the SdH oscillations and the effective masses for both the lighter (HHl) and heavier (HHh) heavy-hole spin subbands independently. Our method has the advantage that it does not require assumptions regarding the band structure, namely, the parabolicity of the spin subbands for determining their effective masses. The masses we find are in good agreement with the results of subband calculations. The data and calculations also provide clear evidence for the strong nonparabolicity of the HHh band.

Our samples were grown on GaAs (100) substrates by MBE and contain modulation-doped 2D hole systems that are confined to either a 20 nm-wide GaAs square quantum well or a GaAs/AlGaAs heterojunction. The square well is flanked on each side by undoped $\text{Al}_{0.3}\text{Ga}_{0.7}\text{As}$ spacer layers. On the front (surface) side, a Be-doped layer (Be concentration of $2.6 \times 10^{18} \text{ cm}^{-3}$) of $\text{Al}_{0.3}\text{Ga}_{0.7}$ follows the 21 nm thick $\text{Al}_{0.3}\text{Ga}_{0.7}$ spacer

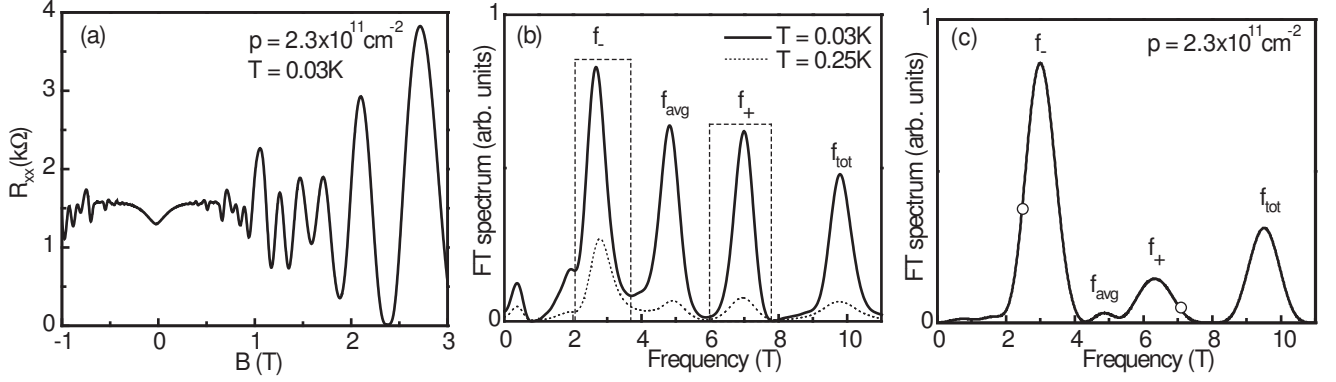


FIG. 1: (a) Observed Shubnikov-de Haas oscillations for a 2D hole system confined to a (100) GaAs/AlGaAs heterojunction. (b) The Fourier spectrum of the oscillations (in the range $0.3T \leq B \leq 3T$) at two different temperatures. The dashed boxes show the square windows applied to isolate the f_- and f_+ peaks before obtaining the inverse Fourier transforms which are shown in the insets in Fig. 2. (c) Fourier spectrum of calculated magneto-oscillations. The open circles indicate the expected peak positions according to the calculated spin subband densities at zero magnetic field (see text).

layer. The $\text{Al}_{0.3}\text{Ga}_{0.7}\text{As}/\text{GaAs}$ interface in the heterojunction sample is separated from a 16 nm thick Be-doped $\text{Al}_{0.3}\text{Ga}_{0.7}\text{As}$ layer (Be concentration of $3.5 \times 10^{18} \text{ cm}^{-3}$) by a 25 nm $\text{Al}_{0.3}\text{Ga}_{0.7}\text{As}$ spacer layer. In order to reduce Be diffusion and migration during the MBE growth, and hence increase the quality of the samples, the substrate temperature was lowered to 550°C from 640°C before doping. In addition, for the square well sample, the doping was done on the front side of the well only unlike previous samples, which had doping on both the front and the substrate sides. We fabricated Hall bar patterns on all the samples and used In/Zn alloyed at 440°C for the ohmic contacts. Metal gates were deposited on the front and the back of the samples to control the density. The typical low temperature mobility for the square well sample is $2.6 \times 10^5 \text{ cm}^2/\text{Vs}$ at a 2D hole density of $p = 1.7 \times 10^{11} \text{ cm}^{-2}$ and for the heterojunction sample it is $7.7 \times 10^4 \text{ cm}^2/\text{Vs}$ at $p = 2.3 \times 10^{11} \text{ cm}^{-2}$. Longitudinal (R_{xx}) and transverse (R_{xy}) magneto-resistances were measured, as a function of the perpendicular magnetic field (B), at $T \approx 30 \text{ mK}$ via a standard low frequency lock-in technique.

Figure 1(a) shows the low-field SdH oscillations for the heterojunction sample. The beating pattern in the oscillations indicates that the two spin subbands are non-degenerate. The FT spectrum of the oscillations, shown in Fig. 1(b), exhibits four dominant peaks at frequencies f_- , f_{avg} , f_+ , and f_{tot} , with the relation $f_{\text{tot}} = f_+ + f_- = 2f_{\text{avg}}$. The f_{tot} frequency, when multiplied by e/h , matches well the total 2D hole density deduced from the Hall resistance (e is the electron charge and h is Planck's constant). The two peaks at f_- and f_+ correspond to the SdH oscillations of the holes in individual spin subbands although, as discussed below, their positions times e/h do not exactly give the spin subband densities. As we also discuss later in the text, the presence of a peak at f_{avg} is related to this anomalous behavior.

We note that the f_{avg} peak is observed in all our GaAs (100) 2D hole samples, including the square well sample which shows an FT spectrum qualitatively similar to Fig. 1(b). In the remainder of the paper we concentrate on the data from the heterojunction sample as it shows a much higher spin splitting than the square well.

We first compare the measured FT spectrum of the SdH oscillations with that of calculated magneto-oscillations of the density of states (DOS) at the Fermi energy (E_F) [16, 17]. We obtain the Landau fan chart at $B > 0$ by evaluating an $8 \times 8 \mathbf{k} \cdot \mathbf{p}$ Hamiltonian that fully takes into account SO coupling due to both the structure inversion asymmetry of the GaAs/AlGaAs heterojunction as well as the bulk inversion asymmetry of the underlying zinc blende structure [11, 18]. In our calculations we assumed that the system formed an accumulation layer. For such systems Stern [19] pointed out that the Hartree potential depends on the concentration of minority impurities. We assumed that the concentration of unintentional minority impurities in the GaAs layer was $1 \times 10^{14} \text{ cm}^{-3}$ and we used a spacer width of 25 nm; both assumptions are consistent with our sample parameters. We note that one should not expect a one-to-one correspondence between the measured SdH oscillations and the calculated magneto-oscillations of the DOS at E_F . For example, the amplitude of the oscillations which determine the amplitudes of the FT spectrum peaks are different from the SdH oscillations. However, the peak positions in the FT spectrum – the quantities we are interested in here – are not affected by these details [16, 17].

Figure 1(c) shows the FT spectrum of the calculated DOS magneto-oscillations for the sample parameters of Figs. 1(a) and (b), i.e., a heterojunction sample with $p = 2.3 \times 10^{11} \text{ cm}^{-2}$. The spectrum shows three main peaks, marked by f_- , f_+ , and f_{tot} . The positions of these peaks are in good agreement with the corresponding three peaks in the experimental data [Fig. 1(b)].

The f_{avg} peak is also seen, albeit with a smaller amplitude, in the FT spectrum of the calculated magneto-oscillations. In Fig. 1(c) we have indicated, by open circles, the positions of FT peaks expected from the relation $f = (h/e)p_{\pm}$, where $p_{\pm}$ are the densities of the two spin subband densities calculated at $B = 0$ [4]. It is evident that the frequencies f_{-} and f_{+} do not directly give the spin subband densities via the relation $p_{\pm} = (e/h)f_{\pm}$. This anomalous behavior, like the unexpected peak at f_{avg} , reflects the fact that the spin precession along the cyclotron orbits becomes nonadiabatic if the SO coupling in some parts of $\mathbf{k}_{\parallel}$ space is sufficiently weak [20]. Qualitatively, one can argue that the peak at f_{avg} is due to the presence of cyclotron orbits in which the holes move half the time along the constant energy contour of the HHh band and then switch to the HHI contour [16]. This simplified picture cannot explain, however, that the peaks at $f_{\pm}$ do not obey the relation $f_{\pm} = (h/e)p_{\pm}$. We remark that anomalous magneto-oscillations were observed also in GaAs (311)A 2D electrons and holes [16, 20].

We now concentrate on our results for the effective masses of the HHI and HHh spin subbands. In a 2D system with only one spin subband occupied, or with degenerate subbands, the variation in the amplitude ΔR_{xx} of the SdH oscillations with temperature T is commonly used to determine the carrier effective mass m^* . This is done by fitting ΔR_{xx} to the Dingle factor, $\xi/\sinh \xi$, where $\xi \equiv 2\pi^2 k_B T / (\hbar \omega_c)$ and $\omega_c = eB/m^*$ [21, 22]. Here m^* is the fitting parameter. In our system however, due to the spin splitting of the subbands giving rise to beating patterns in the SdH oscillations, the two masses cannot be deduced directly by fitting ΔR_{xx} to a Dingle factor. In the SdH experiments performed by Eisenstein *et al.* [2] on GaAs (100) 2D holes, the authors assigned the low field oscillations (with frequency f_{-}) to the SdH effect of the spin subband with the lighter mass, and the oscillations at higher fields (with frequency f_{tot}) to the total 2D hole density. They then determined the mass for HHI, m_{-}^* , by fitting the temperature dependence of the low field oscillations to a Dingle factor. To deduce the HHh mass, m_{+}^* , they assumed that the two spin subbands have parabolic dispersion curves $E_{\pm}(\mathbf{k}_{\parallel}) = \hbar^2 k_{\parallel}^2 / (2m_{\pm}^*)$, where $\mathbf{k}_{\parallel}$ is the in-plane wave vector and $m_{\pm}^*$ are constants independent of the energy E . This model implies the relation $m_{-}^*/m_{+}^* = f_{-}/(f_{\text{tot}} - f_{-})$ which was used in Ref. [2] to obtain m_{+}^* .

In our study, the FT spectrum of the oscillations allows us to independently determine $m_{\pm}^*$ for the two spin subbands. We isolated the individual peaks, f_{-} and f_{+} for HHI and HHh, with square windows [Fig. 1(b)] and calculated their inverse FT [23]. The insets in Figs. 2(a) and (b) show the inverse transform for each of these peaks. The SdH oscillations in these insets can then be attributed to the HHI and HHh spin subbands, respectively. The main parts of Fig. 2 show the temperature variation of the amplitude of these oscillations. We fitted this variation at particular B values to a Dingle factor for each subband [Figs. 2(a) and (b)] and deduced the m^*

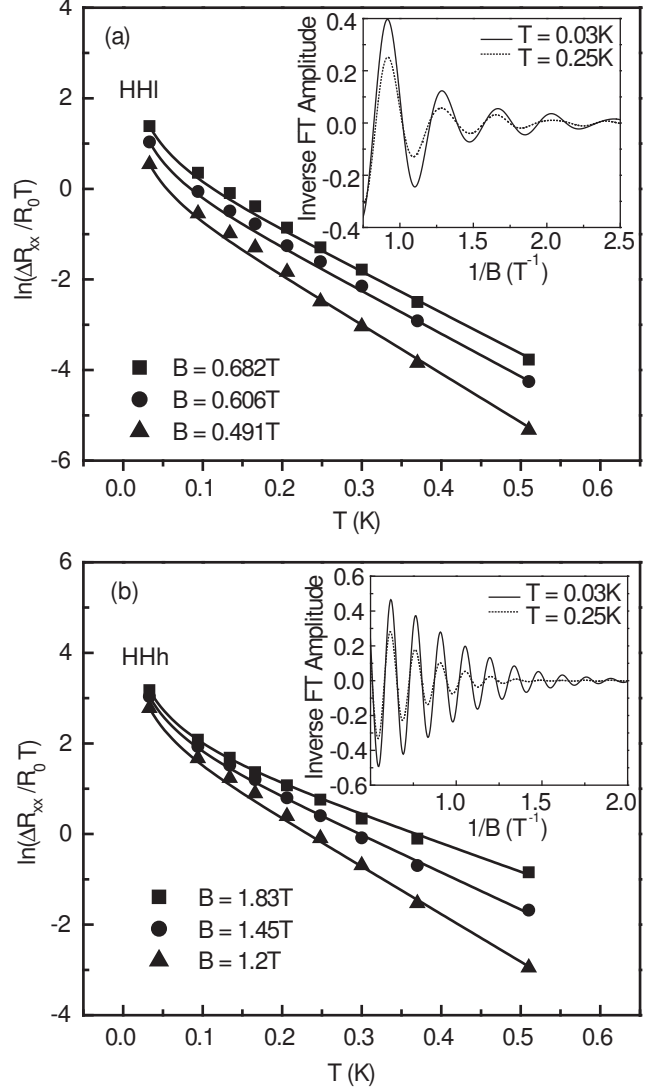


FIG. 2: Variation of ΔR_{xx} with temperature and its fit to the Dingle factor with m^* as the fitting parameter for (a) the HHI and (b) the HHh subbands, respectively. Insets in (a) and (b): After isolating the peaks f_{-} and f_{+} by square windows [see Fig 1(b)], inverse FT is performed on these peaks separately to deduce SdH oscillations of the HHI and HHh subbands.

values as the fitting parameters. Figure 3 shows m^* values determined as a function of B for a hole density of $2.3 \times 10^{11} \text{ cm}^{-2}$. The amplitude variation of the oscillations fitted to the Dingle factor at different values of B should in principle give the same mass. In our system however, m_{-}^* has a strong, nearly linear dependence on the value of B at which the variation of R_{xx} with temperature is analyzed. Only m_{+}^* is approximately independent of B . The origin of the field dependence of m_{-}^* which was also seen in Ref. [2], remains unknown. Linear extrapolation of the data to $B = 0$ (dashed lines in Fig. 3), suggests $m_{+}^* \simeq 0.9 m_0$ and $m_{-}^* \simeq 0.2 m_0$, where m_0 is the mass of free electrons. Note that the ra-

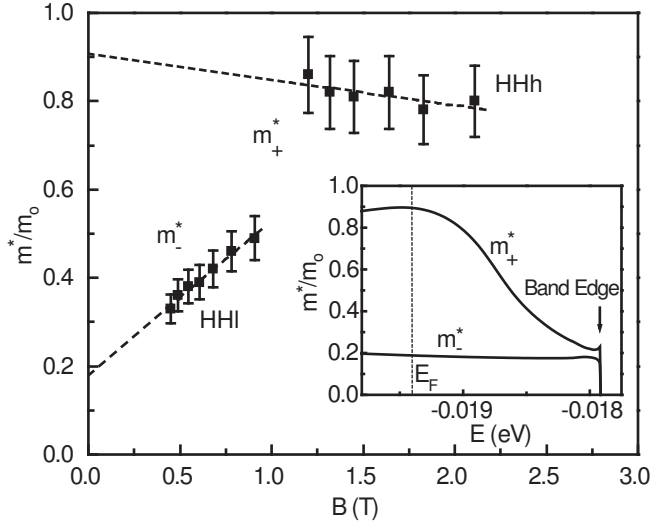


FIG. 3: Values for m_-^* and m_+^* for the HHL and HHh subbands, deduced from fits of SdH oscillation amplitudes to the Dingle factor for the heterojunction sample, with $p = 2.3 \times 10^{11} \text{ cm}^{-2}$ (m_0 is the free electron mass). Inset: m^* calculated from the subband structure at $B = 0$.

tio of the hole densities of the two subbands is not equal to the ratio of their masses. Hence, in general it cannot be assumed that the bands are parabolic and, in particular, m_-^* cannot be deduced from the ratio of the spin subband densities and m_-^* .

We determined m^* at different hole densities ranging from 2.0 to $2.4 \times 10^{11} \text{ cm}^{-2}$ for the heterojunction sample, where we used front and back gate biases to vary the density. The qualitative trends were similar in all cases. The strong dependence of m_-^* on B was observed at all densities and m_+^* was found to be relatively independent of B . Quantitatively, m_+^* ranged from 0.75 to 0.91 and m_-^* extrapolated to a $B = 0$ value between 0.18 to 0.25 in this density range.

We compare the measured effective masses with an energy-dependent DOS effective mass

$$\frac{m_{\pm}^*(E)}{m_0} = \frac{1}{\pi} \frac{\hbar^2}{2m_0} \int d^2 k_{\parallel} \delta[E - E_{\pm}(\mathbf{k}_{\parallel})] \quad (1)$$

for the two spin subbands. Equation (1) gives the effective mass $m_{\pm}^*(E)$ one needs locally at energy E to ap-

proximate $E_{\pm}(\mathbf{k}_{\parallel})$ by a parabolic dispersion which yields the same DOS like $E_{\pm}(\mathbf{k}_{\parallel})$. Our numerical calculations of $E_{\pm}(\mathbf{k}_{\parallel})$ follow Ref. [11]. We then evaluate Eq. (1) by means of analytical quadratic Brillouin zone integration [24]. We remark that the SdH oscillations are an effect taking place at E_F . Therefore, the DOS m^* , defined by Eq. (1) is the appropriate quantity for comparison with the effective mass deduced experimentally from the temperature dependence of the SdH oscillations. However, one should not expect to find a one-to-one correspondence between experiment and theory because the temperature dependence of magneto-oscillations in 2D systems can be more complicated than implicitly assumed by the Dingle formula [25, 26].

The inset in Fig. 3 shows the DOS effective mass calculated for $p = 2.3 \times 10^{11} \text{ cm}^{-2}$. The subband edge is at -17.9 meV and E_F at -19.4 meV . We obtain an effective mass at E_F of $0.9 m_0$ and $0.2 m_0$ for the HHh and HHL bands, respectively. This is in good agreement with our experimental results (Fig. 3). From the curve for the heavier mass, we see that the HHh band is highly nonparabolic. We note that symmetry requires that in a Taylor expansion of the subband dispersion $E_{\pm}(\mathbf{k}_{\parallel})$, the $B = 0$ spin splitting is characterized by terms proportional to odd powers of $\mathbf{k}_{\parallel}$. Only the spin-independent terms in the Taylor expansion are proportional to even powers of $\mathbf{k}_{\parallel}$ [27]. In 2D *hole* systems the odd-power terms give rise to a spin splitting that is comparable in magnitude to the spin-independent part of the subband dispersion [12, 13, 14, 15]. The spin-split subbands thus have nonparabolic dispersion curves with strongly spin-dependent masses. We remark that spin-split *electron* subbands can usually be characterized by the same value of m^* because in the electron case, spin splitting represents only a small correction to the spin-independent part of the subband dispersion [11].

In conclusion, we have measured SdH oscillations in GaAs (100) 2D holes. Through Fourier analysis of the oscillations, we determined the splitting as well as the effective masses of the two spin subbands. The results are in good agreement with the calculations. There remain however, some open questions regarding the origin of the average peak observed in the FT spectrum and the dependence of experimentally determined mass values on B , especially for m_-^* .

We thank the DOE, ARO and NSF for support.

- [1] H. L. Stormer, Z. Schlesinger, A. Chang, D. C. Tsui, A. C. Gossard, and W. Wiegmann, Phys. Rev. Lett. **51**, 126 (1983).
- [2] J. P. Eisenstein*, H. L. Strmer, V. Narayanamurti, A. C. Gossard, and W. Wiegmann, Phys. Rev. Lett. **53**, 2579 (1984).
- [3] A. D. Wieck, E. Batke, D. Heitmann, J. P. Kotthaus, and E. Bangert, Phys. Rev. Lett. **53**, 493 (1984).

- [4] See, e.g., R. Winkler, *Spin-Orbit Coupling Effects in Two-Dimensional Electron and Hole Systems*, (Springer, Berlin, 2003), and references therein.
- [5] See, e.g., G. A. Prinz, Physics Today **48**, 58 (1995); J. L. Simonds, Physics Today **48**, 26 (1995); D. D. Awschalom and J. M. Kikkawa, Physics Today, **52**, 33 (1999).
- [6] S. Datta and B. Das, Appl. Phys. Lett. **56**, 665 (1990).
- [7] A. F. Morpurgo, J. P. Heida, T. M. Klapwijk, B. J. van

- Wees, and G. Borghs, Phys. Rev. Lett. **80**, 1050 (1998).
- [8] J-B Yau, E. P. De Poortere, and M. Shayegan, Phys. Rev. Lett. **88**, 146801 (2002).
 - [9] J. P. Lu, J. B. Yau, S. P. Shukla, M. Shayegan, L. Wissinger, U. Rössler, and R. Winkler, Phys. Rev. Lett. **81**, 1282 (1998).
 - [10] S. J. Papadakis, E. P. De Poortere, H. C. Manoharan, M. Shayegan, and R. Winkler, Science, **283**, 2056 (1999); Physica **E9**, 31 (2001).
 - [11] R. Winkler and U. Rössler, Phys. Rev. B **48**, 8918 (1993).
 - [12] D. A. Broido and L. J. Sham, Phys. Rev. B **31**, 888 (1985).
 - [13] T. Ando, J. Phys. Soc. Jpn. **54**, 1528 (1985).
 - [14] U. Ekenberg and M. Altarelli, Phys. Rev. B **32**, 3712 (1985).
 - [15] E. Bangert and G. Landwehr, Superlatt. Microstruct. **1**, 363 (1985)
 - [16] R. Winkler, S. J. Papadakis, E. P. De Poortere, and M. Shayegan, Phys. Rev. Lett. **84**, 713 (2000).
 - [17] R. Winkler, S. J. Papadakis, E. P. De Poortere, J. P. Lu and M. Shayegan, Physica B **298**, 13 (2001).
 - [18] H.-R. Trebin, U. Rössler, and R. Ranvaud, Phys. Rev. B **20**, 686 (1979).
 - [19] F. Stern, Phys. Rev. Lett. **33**, 960 (1974).
 - [20] S. Keppeler and R. Winkler, Phys. Rev. Lett. **88**, 046401 (2002).
 - [21] R. B. Dingle, Proc. R. Soc. A **211**, 517 (1952).
 - [22] E.N. Adams and T.D. Holstein, J. Phys. Chem. Solids, **10**, 254 (1959).
 - [23] For the f_- peak, the low frequency shoulder can be included or ignored when applying the square window. The inverse FT showed a slight dependence on where exactly the window was applied. However, the portion of the inverse FT which exhibited this dependency was not used in further analysis.
 - [24] R. Winkler, J. Phys.: Condens. Matter **5**, 2321 (1993).
 - [25] F. F. Fang, A. B. Fowler, and A. Hartstein, Phys. Rev. B **16**, 4446 (1977).
 - [26] See for example T. Champel, Phys. Rev. B **64**, 054407 (2001) and references therein.
 - [27] In inversion asymmetric systems we can also have spin-independent terms proportional to odd powers of $k_{\parallel}$. However, it is not possible to have spin-dependent terms proportional to even powers of $k_{\parallel}$.